

applicant.

Form PTO-1449
(REV. 7-80)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

**LIST OF PRIOR ART
CITED BY APPLICANT**

(Use several sheets if necessary)

Attv. Docket No.
FIS920030221US1

Serial No.
10/605,227

Applicants
Cheng, et al.

Filing Date
9/16/03

Group Art Unit
2822

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

KR		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs". 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.
		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress". International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application". International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
		A. Shimzu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement". International Electron Devices Meeting, IEEE, March 2001.
		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors". IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.
		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures". Paper 6.2, pp. 140-143.
		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors". IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-73.
		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing". Pp. 14-15.
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors". Pp. 1-5.
↓		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems". 2003 IEEE GaAs Digest, pp. 263-66.
KR		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling". IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

EXAMINER

/Kiesha Rose/ (07/07/2006)

DATE CONSIDERED

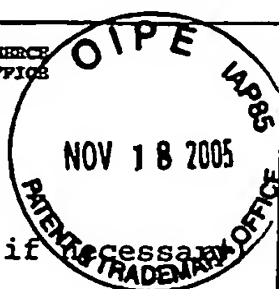
07/07/2006

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KR

B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs". IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.

KR

H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistor for Bi-CMOS". IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Docket Number (Optional)	Application Number 10/605 227
	Applicant(s) K. Cheng	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		4,958,213	9-18-90	Eklund, et al.	257	378	
		5,006,913	4-9-91	Sugahara, et al.	257	67	
		5,060,030	10-22-91	Hoke, et al.	257	194	
		5,081,513	1-14-92	Jackson, et al.	257	57	
KR		5,108,843	4-28-92	Ohtaka, et al.	428	2446	

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		US 2002/0086497 A1	7-4-02	Kwok	438	424	
		US 2002/0090791 A1	7-11-02	Doyle, et al.	438	396	
		US 2003/0032261 A1	2-13-03	Yeh, et al.	438	451	
KR		US 2003/0040158 A1	2-27-03	Saitoh	438	279	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
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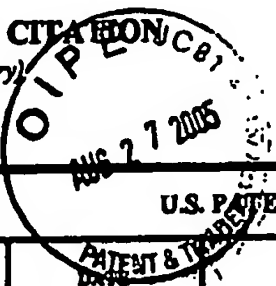
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
		P. Ootanka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

EXAMINER K. Rose	DATE CONSIDERED 9/13/05
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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Docket Number (Optional) F18920030221 US1	Application Number 10/605 227
	Applicant(s) K. Chong et al	
	Filing Date 9/16/2003	Group Art Unit 2822



U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		3,602,841	8-31-71	McGroddy	331	107G	
I		4,665,415	5-12-87	Esaki, et al.	257	190	
I		4,853,076	8-1-89	Tsaur, et al.	438	479	
I		4,855,245	8-8-89	Neppl, et al.	438	207	
KR		4,952,524	8-28-90	Lee, et al.	438	437	

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		US 2001/0009784 A1	7-26-01	Ma, et al.	438	197	
I		US 2002/0063292 A1	5-30-02	Armstrong, et al.	257	367	
I		US 2002/0074598 A1	6-20-02	Doyle, et al.	257	345	
KR		US 2002/0086472	7-4-02	Roberds, et al.	438	197	

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		JP64-76755	03-1989	Japan				

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
		Kern Rlm, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
		Kern Rlm, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional)	Application Number 10/605227
	Applicant(s) K Cheng	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		5,134,085	7-28-92	Gligen, et al.	438	A40	
		5,310,446	5-10-94	Konishi, et al.	117	58	
		5,354,695	10-11-94	Leedy	438	411	
		5,371,399	12-6-94	Burroughes, et al.	257	451	
KR		5,391,510	2-21-95	Hsu, et al.	438	301	

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		US 2003/0057184 A1	3-27-03	Yu, et al.	216	79	
KR		US 2003/0067035 A1	4-10-03	Tews, et al.	257	333	

FOREIGN PATENT DOCUMENTS

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							YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and Its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
		A. Shimizu, et al., "Local Mechanical Stress Control (LMC): A New Technique for CMOS Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

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	Applicant(s) R. Chen	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		5,459,346	10-17-95	Asakawa, et al.	257	347	
I		5,471,948	12-5-95	Burroughes, et al.	438	93	
I		5,557,122	9-17-96	Shrivastava, et al.	257	309	
I		5,561,302	10-1-96	Candelaria	257	24	
KR		5,565,697	10-15-96	Asakawa, et al.	257	347	

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RR		5,571,741	11-5-96	Leedy	438	27	
		5,592,007	1-7-97	Leedy	257	347	
		5,592,018	1-7-97	Leedy	257	619	
		5,670,798	9-23-97	Schetzina	257	96	
RR		5,679,965	10-21-97	Schetzina	257	103	

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and Its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.
		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

EXAMINER H. J. Rose	DATE CONSIDERED 9/13/05
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101605227

Applicant(s)

K. Cheng

Filing Date

9/16/2003

Group Art Unit

2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		5,683,934	11-4-97	Candelaria	438	151	
		5,840,593	11-24-98	Leedy	438	6	
		5,861,651	1-19-99	Brasen, et al.	257	411	
		5,880,040	3-9-99	Sun, et al.	438	769	
KR		5,940,716	8-17-99	Jin, et al.	438	424	

U.S. PATENT APPLICATION PUBLICATIONS

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		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

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	Applicant(s) K Chen	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		5,940,736	8-17-99	Brady, et al.	438	787	
		5,946,559	8-31-99	Leedy	438	157	
		5,960,297	9-28-99	Saki	438	424	
		5,989,978	11-23-99	Peldous	438	436	
KR		6,008,126	12-28-99	Leedy	438	667	

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

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		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.
		H. Wurzer, et al., "Annealing of Degraded n-p-n Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		6,025,280	2-15-00	Brady, et al.	438	762	
		6,046,464	4-4-00	Schetzina	257	96	
		6,066,545	5-23-00	Doshi, et al.	438	439	
		6,090,684	7-18-00	Ishitsuka, et al.	438	424	
KR		6,107,143	8-22-00	Park, et al.	438	296	

U.S. PATENT APPLICATION PUBLICATIONS

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		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.
		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistor for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		6,117,722	9-12-00	Wuu, et al.	438	238	
		6,133,071	10-17-00	Nagai	438	122	
		6,165,383	12-26-00	Chou	252	301.16	
		6,221,735	4-24-01	Manley, et al.	438	426	
KR		6,228,694	5-8-01	Doyle, et al.	438	199	

U.S. PATENT APPLICATION PUBLICATIONS

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U.S. PATENT DOCUMENTS

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KR		6,246,095	6-12-01	Brady, et al.	257	411	
		6,255,169	7-3-01	Li, et al.	438	264	
		6,261,964	7-17-01	Wu, et al.	438	705	
		6,265,317	7-24-01	Chiu, et al.	438	711	
KR		6,274,444	8-14-01	Wang	438	299	

U.S. PATENT APPLICATION PUBLICATIONS

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KR		6,281,532	8-28-01	Doyle, et al.	257	288	
		6,284,623	9-4-01	Zhang, et al.	438	424	
		6,284,626	9-4-01	Kim	438	433	
		6,319,794	11-20-01	Akatsu, et al.	438	424	
KR		6,361,885	3-26-02	Chou	428	690	

U.S. PATENT APPLICATION PUBLICATIONS

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EXAMINER

R. Rose

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	Applicant(s) K. Chan	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		6,362,082	3-26-02	Doyle, et al.	438	523	
		6,368,931	4-9-02	Kuhn, et al.	438	359	
		6,403,486	6-11-02	Lou	438	694	
		6,403,975	6-11-02	Brunner, et al.	257	15	
KR		6,406,973	6-18-02	Lee	438	416	

U.S. PATENT APPLICATION PUBLICATIONS

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KR		6,461,936	10-8-02	von Ehrenwall	438	424	
		6,476,462	11-5-02	Shimizu, et al.	257	627	
		6,483,171	11-19-02	Forbes, et al.	257	627	
		6,493,497	12-10-02	Ramdani, et al.	385	131	
KR		6,498,358	12-24-02	Lach, et al.	257	183	

U.S. PATENT APPLICATION PUBLICATIONS

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							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER K. Rose	DATE CONSIDERED 9/13/05
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

Application Number

10/605227

Applicant(s)

K. Chang

Filing Date

9/16/2003

Group Art Unit

2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		6,501,121	12-31-02	Yu, et al.	257	310	
		6,506,652	1-14-03	Jan, et al.	438	303	
		6,509,618	1-21-03	Jan, et al.	257	413	
		6,521,964	2-18-03	Jan, et al.	257	413	
KR		6,531,369	3-11-03	Ozkan, et al.	438	312	

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

K. Rose

DATE CONSIDERED

9/13/05

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional)	Application Number 10/605227
	Applicant(s) K. Chang	
	Filing Date 9/16/2003	Group Art Unit 2822

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KR		6,531,740	3-11-03	Bosco, et al.	257	347	
		6,621,392	9-16-03	Volant, et al.	335	78	
KR		6,635,506	10-21-03	Volant, et al.	438	52	

U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REP	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE

EXAMINER K. Rose	DATE CONSIDERED 9/13/05
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